

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A thermal treatment apparatus comprising:
a furnace for heat-treating a substrate-substrate; and
with the substrate being supported by a substrate support, support for
supporting the substrate in the furnace,

wherein the substrate support has a main body portion and a supporting
portion ~~which is provided on the main body portion and in portion,~~ the supporting portion
being in contact with the substrate, and

the supporting portion is formed from a silicon ~~platelike member having a~~
plate-like member,

~~thickness~~ a thickness of the supporting portion is not less than twice larger
~~than the thickness~~ a thickness of the substrate-substrate and not more than 10 mm, and

the supporting portion is not in contact with a periphery of the substrate.

2-4. (Canceled)

5. (Currently Amended) The thermal treatment apparatus according to claim 1,
wherein a substrate-placing face of the supporting portion, on which the substrate is placed, is
provided coated with an anti-adhesion layer for preventing adhesion between the substrate
and the supporting portion-an amorphous silicon oxide film.

6. (Currently Amended) A thermal treatment apparatus comprising:
a furnace for heat-treating a substratesubstrate, and
with the substrate being supported by a substrate support,support for
supporting the substrate in the furnace,

wherein the substrate support has a main body portion and a supporting portion ~~which is provided on the main body portion and~~ portion, the supporting portion being in contact with the substrate,

the supporting portion is ~~made of silicon,~~ formed from a silicon plate-like member,

a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with a film or films comprising one or more ~~a plural number of~~ materials of including silicon carbide (SiC), silicon nitride (Si_3N_4), polycrystalline silicon, silicon oxide (SiO_2), glassy carbon, and microcrystalline diamond.

7-11. (Canceled)

12. (Currently Amended) The thermal treatment apparatus according to ~~claim~~ 10, claim 6, wherein ~~the uppermost~~ uppermost film of the film or the films is ~~an~~ amorphous silicon oxide (SiO_2) film.

13-14. (Canceled)

15. (Withdrawn-Currently Amended) A method for manufacturing a substrate, comprising:

carrying a substrate into a ~~treatment room;~~ furnace;

supporting the substrate by a supporting portion formed from a silicon ~~platelike member~~ plate-like member having a thickness ~~larger than~~ not less than twice a thickness of the ~~substrate;~~ substrate and not more than 10 mm, the supporting portion not being in contact with a periphery of the substrate;

heat-treating the substrate in the ~~treatment room~~-furnace with the substrate being supported by the supporting portion; and

carrying ~~out~~ the substrate ~~from out of~~ the ~~treatment room~~-furnace.

16. (Withdrawn-Currently Amended) A method for manufacturing a substrate, comprising:

carrying a substrate into a ~~treatment room~~;furnace;

supporting the substrate by a ~~silicon supporting portion~~ supporting portion wherein a ~~substrate placing face, on which the substrate is placed, is coated with a film comprising one or a plural number of materials of silicon carbide (SiC), silicon oxide (SiO₂), glassy carbon, and microcrystalline diamond;~~

heat-treating the substrate in the ~~treatment room~~-furnace with the substrate being supported by the supporting portion; and

carrying ~~out~~ the substrate ~~from out of~~ the ~~treatment room~~-furnace,

wherein the supporting portion is formed from a silicon plate-like member,

a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with a film or films comprising one or more materials including silicon carbide, silicon nitride, polycrystalline silicon, silicon oxide, glassy carbon, and microcrystalline diamond.

17. (Withdrawn-Currently Amended) A method for manufacturing a semiconductor device, comprising:

carrying a substrate into a ~~treatment room~~;furnace;

supporting the substrate by a supporting portion formed from a silicon ~~platelike member~~ plate-like member having a thickness ~~larger than the~~ not less than twice a thickness of the ~~substrate;~~ substrate and not more than 10 mm, the supporting portion not being in contact with a periphery of the substrate;

heat-treating the substrate in the ~~treatment room~~ furnace with the substrate being supported by the supporting portion; and

carrying ~~out the substrate from out of the treatment room~~ the substrate from out of the furnace.

18. (Withdrawn-Currently Amended) A method for manufacturing a semiconductor device, comprising:

carrying a substrate into a ~~treatment room;~~ furnace;

supporting the substrate by a ~~silicon supporting portion~~ supporting portion; wherein a ~~substrate placing face, on which the substrate is placed, is coated with a film comprising one or a plural number of materials of silicon carbide (SiC), silicon oxide (SiO₂), glassy carbon, and microcrystalline diamond;~~

heat-treating the substrate in the treatment room with the substrate being supported by the supporting portion; and

carrying ~~out the substrate from out of the treatment room~~ the substrate from out of the furnace,

wherein the supporting portion is formed from a silicon plate-like member, a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with a film or films comprising one or more materials including silicon carbide, silicon nitride, polycrystalline silicon, silicon oxide, glassy carbon, and microcrystalline diamond.

19. (New) A thermal treatment apparatus comprising:

- a furnace for heat-treating a substrate; and
- a substrate support for supporting the substrate in the furnace,

wherein the substrate support has a supporting portion which is in contact with the substrate and a main body portion which supports the supporting portion,

- the main body portion is formed from a silicon carbide,
- the supporting portion is formed from a silicon plate-like member and a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,
- a diameter of the supporting portion is smaller than a diameter of the substrate,

and

- a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with an amorphous silicon oxide film.

20. (New) A thermal treatment apparatus comprising:

- a furnace for heat-treating a substrate; and
- a substrate support for supporting the substrate in the furnace,

wherein the substrate support has a supporting portion that is in contact with the substrate and a plate that supports the supporting portion and a main body portion which supports the plate,

- the supporting portion is formed from a silicon plate-like member and a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,
- a diameter of the supporting portion is smaller than a diameter of the substrate and a diameter of the plate, and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with an amorphous silicon oxide film.

21. (New) The thermal treatment apparatus according to claim 20, wherein the plate and the main body portion are formed from a silicon carbide.